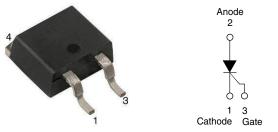
Vishay Semiconductors

# **Thyristor Surface-Mount, Phase Control SCR, 16 A**



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D<sup>2</sup>PAK 2L (TO-263AB 2L)

### LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS								
I <sub>T(AV)</sub>	16 A							
V <sub>DRM</sub> /V <sub>RRM</sub>	1600 V							
V <sub>TM</sub>	1.25 V							
I <sub>GT</sub>	45 mA							
TJ	-40 °C to +125 °C							
Package	D <sup>2</sup> PAK 2L (TO-263AB 2L)							
Circuit configuration	Single SCR							

#### FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- AEC-Q101 qualified
- Meets JESD 201 class 2 whisker test
- Flexible solution for reliable AC power rectification
- Easy control peak current at charger power up to reduce passive / electromechanical components
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### APPLICATIONS

- On-board and off-board EV / HEV battery chargers
- Renewable energy inverters

#### DESCRIPTION

The VS-25TTS16S2L-M3 high voltage series of silicon controlled rectifiers is specifically designed for medium power switching and phase control applications.

### **MECHANICAL DATA**

Case: D<sup>2</sup>PAK 2L (TO-263AB 2L)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

OUTPUT CURRENT IN TYPICAL APPLICATIONS									
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS						
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 $\mu m)$ copper	3.5	5.5							
Aluminum IMS, R <sub>thCA</sub> = 15 °C/W	8.5	13.5	A						
Aluminum IMS with heatsink, $R_{thCA} = 5 \text{ °C/W}$	16.5	25.0							

Note

•  $T_A = 55 \text{ °C}, T_J = 125 \text{ °C}, \text{ footprint } 300 \text{ mm}^2$ 

MAJOR RATINGS AND CHARACTERISTICS									
PARAMETER	TEST CONDITIONS	VALUES	UNITS						
I <sub>T(AV)</sub>	Sinusoidal waveform	16	٨						
I <sub>RMS</sub>		25	A						
V <sub>RRM</sub> /V <sub>DRM</sub>		1600	V						
I <sub>TSM</sub>		350	А						
V <sub>T</sub>	16 A, T <sub>J</sub> = 25 °C	1.25	V						
dV/dt		500	V/µs						
dl/dt		150	A/µs						
TJ		-40 to +125	°C						

VOLTAGE RATINGS			
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> , AT 125 °C mA
VS-25TTS16SLHM3	1600	1600	10

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HALOGEN

FREE



# VS-25TTS16S2LHM3

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ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEO	T CONDITIONS	VAL	UNITS		
PARAMETER	STMBUL	163	CONDITIONS	TYP.	UNITS		
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 93 °C, 180° c	onduction half sine wave	1	6		
Maximum RMS on-state current	I <sub>RMS</sub>			2	5	А	
Maximum peak, one-cycle,		10 ms sine pulse, r	ated V <sub>RRM</sub> applied	3	00	A	
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, r	no voltage reapplied	3	50		
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	10 ms sine pulse, r	ated V <sub>RRM</sub> applied	4	50	A <sup>2</sup> s	
	1-1	10 ms sine pulse, r	630		A-5		
Maximum I²√t for fusing	l²√t	t = 0.1 ms to 10 ms	6300		A²√s		
Maximum on-state voltage drop	V <sub>TM</sub>	16 A, T <sub>J</sub> = 25 °C		1.25		V	
On-state slope resistance	r <sub>t</sub>	T 105 %C		12.0		mΩ	
Threshold voltage	V <sub>T(TO)</sub>	T <sub>J</sub> = 125 °C	1.0		.0	V	
Maximum reverse and direct lockage surrent	1 /1	T <sub>J</sub> = 25 °C		0	.5		
Maximum reverse and direct leakage current	I <sub>RM</sub> /I <sub>DM</sub>	T <sub>J</sub> = 125 °C	$V_{R} = Rated V_{RRM}/V_{DRM}$	10		1	
Holding current	I <sub>H</sub>	Anode supply = 6 V, resistive load, initial $I_T = 1 \text{ A}$ , $T_J = 25 \text{ °C}$		-	150	mA	
Maximum latching current	١L	Anode supply = 6 V, resistive load, $T_J$ = 25 °C			00		
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J max.$ , linear	to 80 %, V <sub>DRM</sub> = R <sub>g</sub> - k = Open	en 500		V/µs	
Maximum rate of rise of turned-on current	dl/dt			1	A/µs		

TRIGGERING									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Maximum peak gate power	P <sub>GM</sub>		8.0	W					
Maximum average gate power	P <sub>G(AV)</sub>		2.0	vv					
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	А					
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	V					
		Anode supply = 6 V, resistive load, $T_J = -10 \text{ °C}$	60						
Maximum required DC gate current to trigger	I <sub>GT</sub>	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$	45	mA					
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	20						
		Anode supply = 6 V, resistive load, $T_J = -10 \text{ °C}$	2.5						
Maximum required DC gate voltage to trigger	V <sub>GT</sub>	Anode supply = 6 V, resistive load, $T_J = 25 \degree C$	2.0						
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	1.0	V					
Maximum DC gate voltage not to trigger	V <sub>GD</sub>								
Maximum DC gate current not to trigger	I <sub>GD</sub>	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated value	2.0	mA					

SWITCHING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9					
Typical reverse recovery time	t <sub>rr</sub>	T <sub>.1</sub> = 125 °C	4	μs				
Typical turn-off time	tq	1j=125 C	110					

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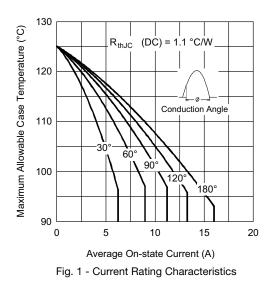


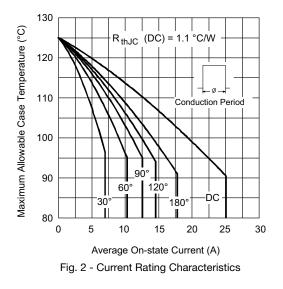
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THERMAL AND MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS						
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C				
Soldering temperature	T <sub>S</sub>	For 10 s (1.6 mm from case)	260					
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	1.1	°C/W				
Typical thermal resistance, junction to ambient (PCB mount)	R <sub>thJA</sub> <sup>(1)</sup>		40	-0/w				
Approximate weight			2	g				
			0.07	oz.				
Marking device		Case style D <sup>2</sup> PAK 2L (TO-263AB 2L)	25TT	S16S				

#### Note

(1) When mounted on 1" square (650 mm<sup>2</sup>) PCB of FR-4 or G-10 material 4 oz. (140 µm] copper 40 °C/W





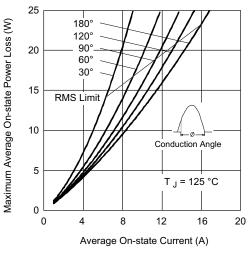
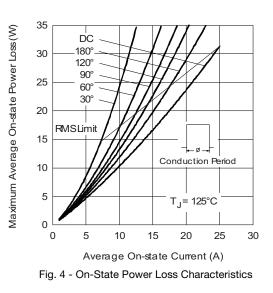


Fig. 3 - On-State Power Loss Characteristics



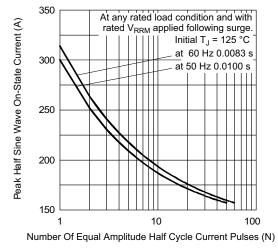
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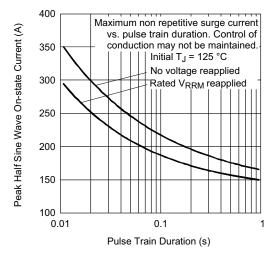
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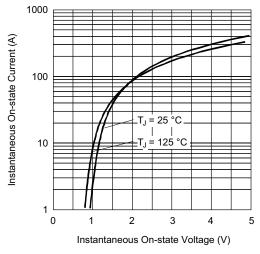
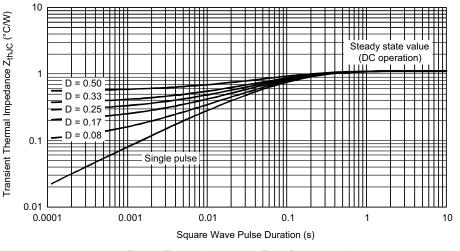


Fig. 7 - On-State Voltage Drop Characteristics





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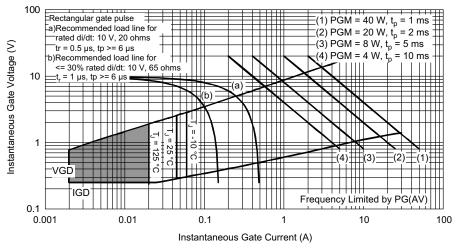


Fig. 9 - Gate Characteristics

### **ORDERING INFORMATION TABLE**

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**SHAY** 

Device code	vs-	25	т	т	s	16	S	2	L	н	М3
	1	2	3	4	5	6	7	8	9	10	(11)
	1 -	· Visł	nay Sen	niconduc	ctors pro	oduct					
	2 -	- Cur	rent rati	ng (25 =	= 25 A)						
	3 -	<ul> <li>Circuit configuration:</li> <li>T = single thyristor</li> </ul>									
	4 -	· Pac	Package: T = $D^2$ PAK (TO-263AB)								
	5 -	. Тур	Type of silicon:								
	6 -		S = standard recovery rectifier Voltage rating: Voltage code x 100 = V <sub>RRM</sub> ——16 = 1600 V								
	7 -	- S =	surface	mounta	able						
	8 -	2 =	true 2 p	in D <sup>2</sup> PA	K						
	9 -	L =	L = tape and reel (left oriented), for different orientation contact factory								
	10 -	• H=	AEC Q	101 qua	lified						
	11 -			ntal digit en-free,		complia	nt, and	termina	tions lea	ad (Pb)-	free

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-25TTS16S2LHM3	800	800	13" diameter reel						

LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?96683						
Part marking information	www.vishay.com/doc?96693						
Packaging information	www.vishay.com/doc?96317						

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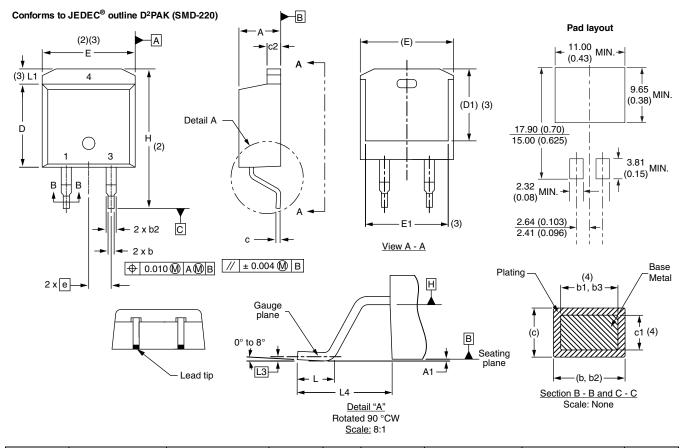
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D<sup>2</sup>PAK 2L (TO-263AB 2L)

#### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STINDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L3	0.25 BSC		0.010 BSC		
c2	1.14	1.65	0.045	0.065			L4	4.78	5.28	0.188	0.208	
D	8.51	9.65	0.335	0.380	2							

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
 (3) Thermal and contain antional within dimension E 1.1, D1 and E1.

<sup>(3)</sup> Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

<sup>(5)</sup> Datum A and B to be determined at datum plane H

<sup>(6)</sup> Controlling dimension: inch

(7) Outline conforms to JEDEC® outline TO-263AB

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